

NTZD3156C

Small Signal MOSFET

20 V, 540 mA / -20 V, -430 mA

Complementary N- and P-Channel
MOSFETs with Integrated Pull Up/Down
Resistor and ESD Protection

Features

- Leading Trench Technology for Low $R_{DS(on)}$ Performance
- High Efficiency System Performance
- Low Threshold Voltage
- Integrated G-S Resistor on Both Devices
- ESD Protected Gate
- Small Footprint 1.6 x 1.6 mm
- These are Pb-Free Devices

Applications

- Load/Power Switching with Level Shift
- Portable Electronic Products such as GPS, Cell Phones, DSC, PMP, Bluetooth Accessories

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	20	V
Gate-to-Source Voltage		V_{GS}	± 6	V
N-Channel Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	540	mA
		$T_A = 85^\circ\text{C}$	390	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	570	
		$T_A = 85^\circ\text{C}$	430	
P-Channel Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	-430	mA
		$T_A = 85^\circ\text{C}$	-310	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	-455	
		$T_A = 85^\circ\text{C}$	-310	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	mW
			250	
Pulsed Drain Current	N-Channel	$t_p = 10$ μs	I_{DM}	mA
			1500	
Operating Junction and Storage Temperature	T_J, T_{STG}		-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)		I_S	350	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq [1 oz] including traces).

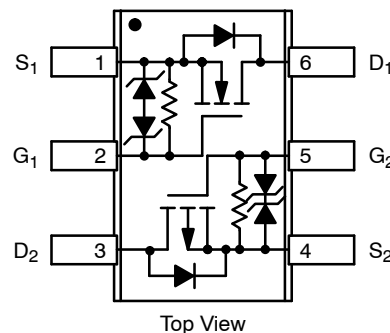


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$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max (Note 1)
N-Channel 20 V	0.55 Ω @ 4.5 V	540 mA
	0.7 Ω @ 2.5 V	
	0.9 Ω @ 1.8 V	
P-Channel -20 V	0.9 Ω @ -4.5 V	-430 mA
	1.2 Ω @ -2.5 V	
	2.0 Ω @ -1.8 V	

PINOUT: SOT-563



SOT-563-6
CASE 463A
STYLE 9

MARKING DIAGRAM



ZC = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTZD3156CT1G	SOT-563	4000 / Tape & Reel
NTZD3156CT2G	SOT-563	4000 / Tape & Reel
NTZD3156CT5G	SOT-563	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTZD3156C

Thermal Resistance Ratings

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	116	°C/W
Junction-to-Ambient – $t = 5$ s (Note 2)		304	

2. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	N	$V_{GS} = 0$ V	$I_D = 250$ μ A	20		V
		P		$I_D = -250$ μ A	-20		
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				20		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	N	$V_{GS} = 0$ V, $V_{DS} = 16$ V	$T_J = 25^\circ\text{C}$		1.0	μ A
		P	$V_{GS} = 0$ V, $V_{DS} = -16$ V			-1.0	
		N	$V_{GS} = 0$ V, $V_{DS} = 16$ V	$T_J = 125^\circ\text{C}$		2.0	μ A
		P	$V_{GS} = 0$ V, $V_{DS} = -16$ V			-5.0	
Gate-to-Source Leakage Current	I_{GSS}	N	$V_{DS} = 0$ V, $V_{GS} = \pm 4.5$ V			± 50	μ A
		P				± 50	

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	N	$V_{GS} = V_{DS}$	$I_D = 250$ μ A	0.45	1.0	V
		P		$I_D = -250$ μ A	-0.45	-1.0	
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				2.0		-mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	N	$V_{GS} = 4.5$ V, $I_D = 540$ mA		0.19	0.55	Ω
		P	$V_{GS} = -4.5$ V, $I_D = -430$ mA		0.39	0.9	
		N	$V_{GS} = 2.5$ V, $I_D = 500$ mA		0.26	0.7	
		P	$V_{GS} = -2.5$ V, $I_D = -300$ mA		0.53	1.2	
		N	$V_{GS} = 1.8$ V, $I_D = 350$ mA		0.36	0.9	
		P	$V_{GS} = -1.8$ V, $I_D = -150$ mA		0.72	2.0	
Forward Transconductance	g_{FS}	N	$V_{DS} = 10$ V, $I_D = 540$ mA		1.46		S
		P	$V_{DS} = -10$ V, $I_D = -430$ mA		1.18		

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	N	$f = 1$ MHz, $V_{GS} = 0$ V $V_{DS} = 16$ V		72		pF
Output Capacitance	C_{OSS}				13		
Reverse Transfer Capacitance	C_{RSS}				10		
Input Capacitance	C_{ISS}	P	$f = 1$ MHz, $V_{GS} = 0$ V $V_{DS} = -16$ V		93		
Output Capacitance	C_{OSS}				15		
Reverse Transfer Capacitance	C_{RSS}				11		

3. Pulse Test: pulse width ≤ 300 μ s, duty cycle $\leq 2\%$

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
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CHARGES, CAPACITANCES AND GATE RESISTANCE

Total Gate Charge	$Q_{G(TOT)}$	N	$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}; I_D = 540\text{ mA}$		1.39	2.5	nC
Threshold Gate Charge	$Q_{G(TH)}$				0.1		
Gate-to-Source Charge	Q_{GS}				0.26		
Gate-to-Drain Charge	Q_{GD}				0.39		
Total Gate Charge	$Q_{G(TOT)}$	P	$V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V}; I_D = -430\text{ mA}$		1.49	2.5	
Threshold Gate Charge	$Q_{G(TH)}$				0.1		
Gate-to-Source Charge	Q_{GS}				0.3		
Gate-to-Drain Charge	Q_{GD}				0.37		

SWITCHING CHARACTERISTICS ($V_{GS} = V$) (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	N	$V_{GS} = 4.5\text{ V}, V_{DD} = 10\text{ V}, I_D = 540\text{ mA}, R_G = 10\ \Omega$		7.7		ns
Rise Time	t_r				5.3		
Turn-Off Delay Time	$t_{d(OFF)}$				21		
Fall Time	t_f				10		
Turn-On Delay Time	$t_{d(ON)}$	P	$V_{GS} = -4.5\text{ V}, V_{DD} = -10\text{ V}, I_D = -430\text{ mA}, R_G = 10\ \Omega$		9.2		
Rise Time	t_r				6.5		
Turn-Off Delay Time	$t_{d(OFF)}$				29		
Fall Time	t_f				19.5		

Drain-Source Diode Characteristics

Forward Diode Voltage	V_{SD}	N	$V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	$I_S = 350\text{ mA}$		0.77	1.2	V
		P		$I_S = -350\text{ mA}$		-0.77	-1.2	
		N	$V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$	$I_S = 350\text{ mA}$		0.65		
		P		$I_S = -350\text{ mA}$		0.63		
Reverse Recovery Time	t_{RR}	N	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}$	$I_S = 350\text{ mA}$		9.4		ns
		P		$I_S = -350\text{ mA}$		14.6		

4. Switching characteristics are independent of operating junction temperatures

N-CHANNEL TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

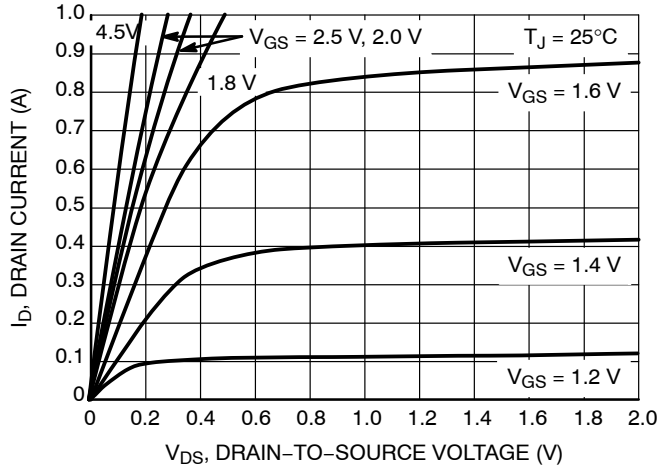


Figure 1. On-Region Characteristics

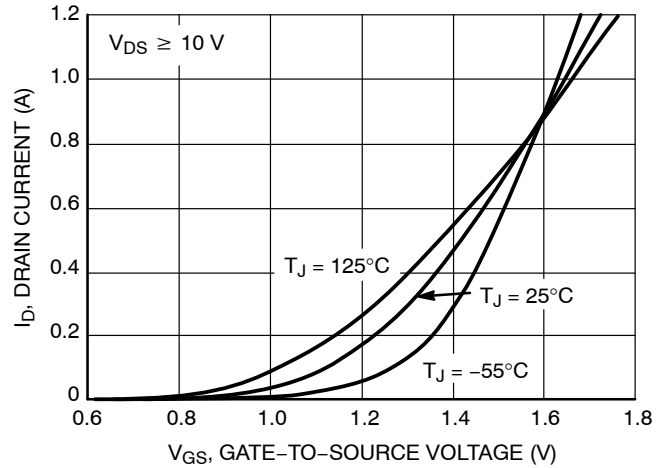


Figure 2. Transfer Characteristics

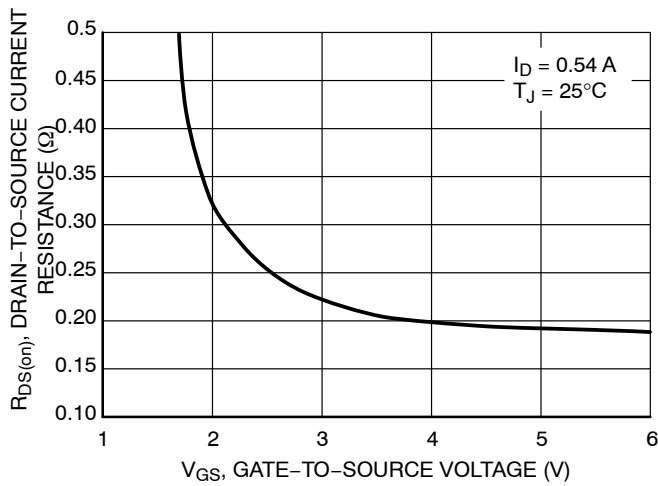


Figure 3. On-Resistance versus Gate-to-Source Voltage

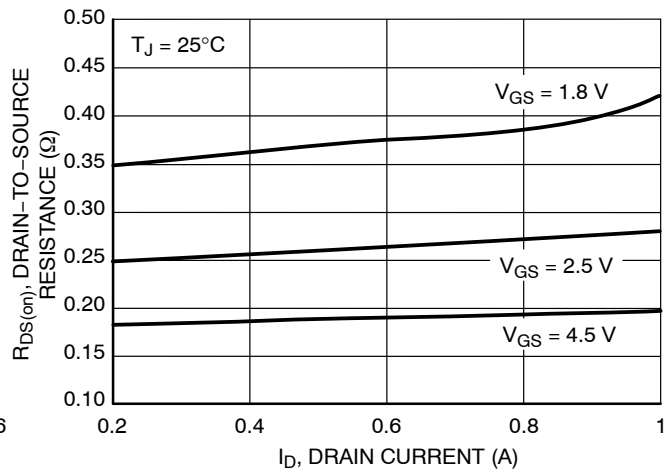


Figure 4. On-Resistance versus Drain Current and Gate Voltage

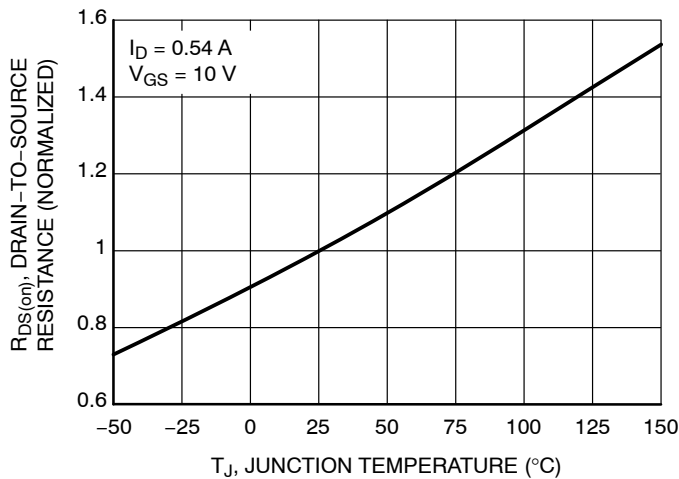


Figure 5. On-Resistance Variation with Temperature

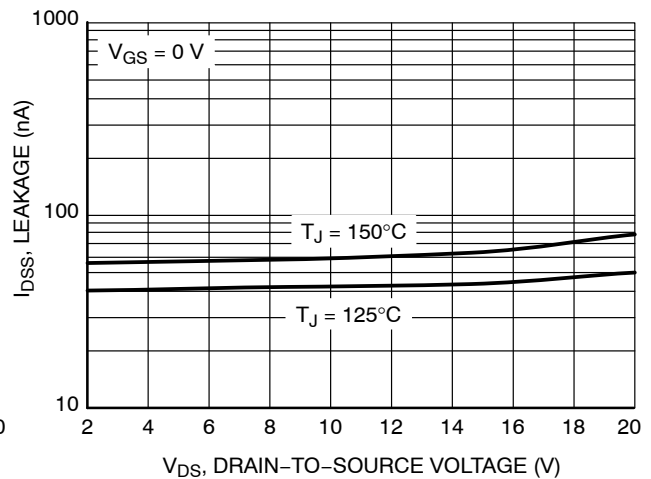


Figure 6. Drain-to-Source Leakage Current versus Voltage

N-CHANNEL TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

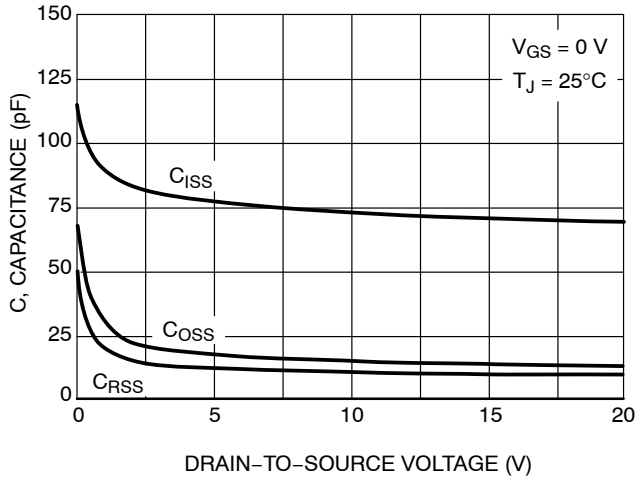


Figure 7. Capacitance Variation

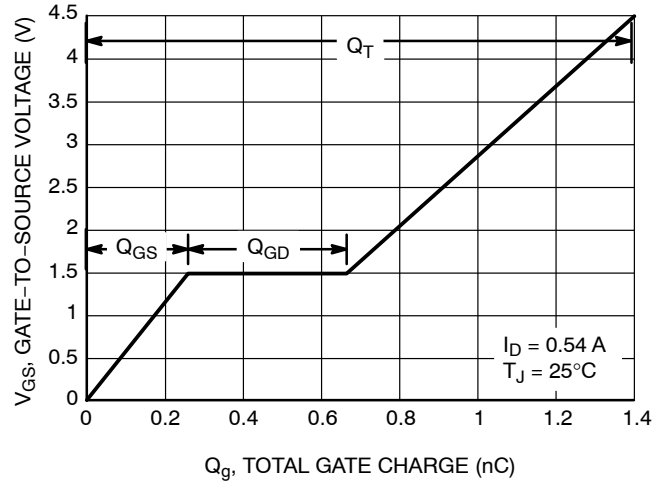


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

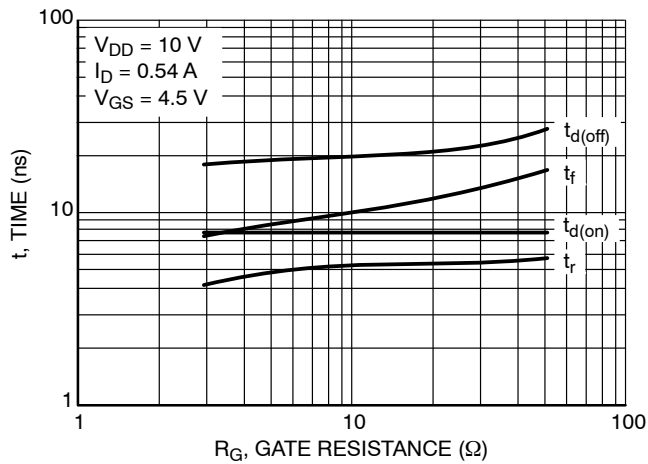


Figure 9. Resistive Switching Time Variation versus Gate Resistance

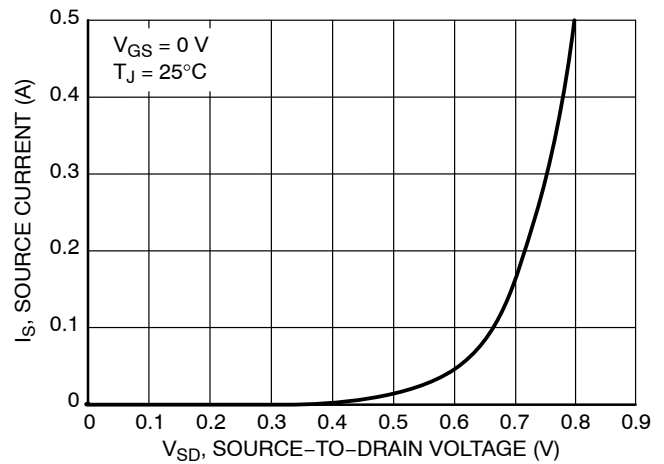


Figure 10. Diode Forward Voltage versus Current

P-CHANNEL TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

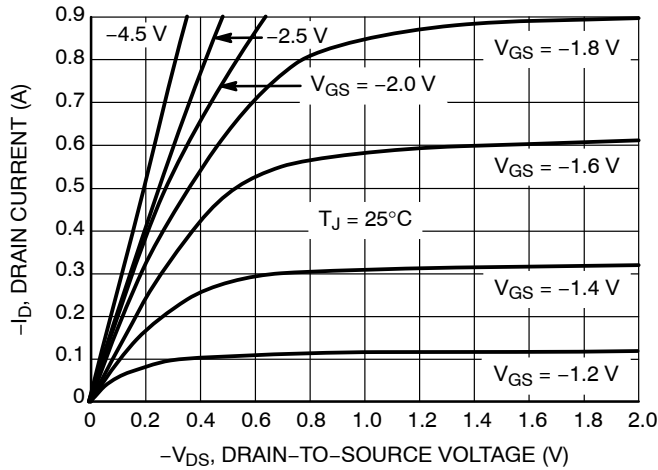


Figure 11. On-Region Characteristics

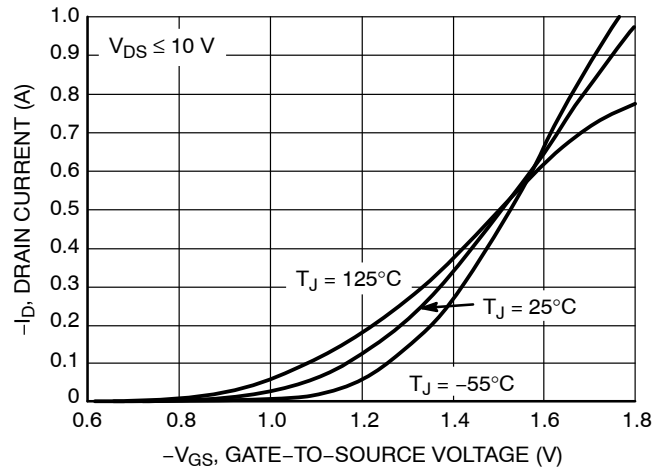


Figure 12. Transfer Characteristics

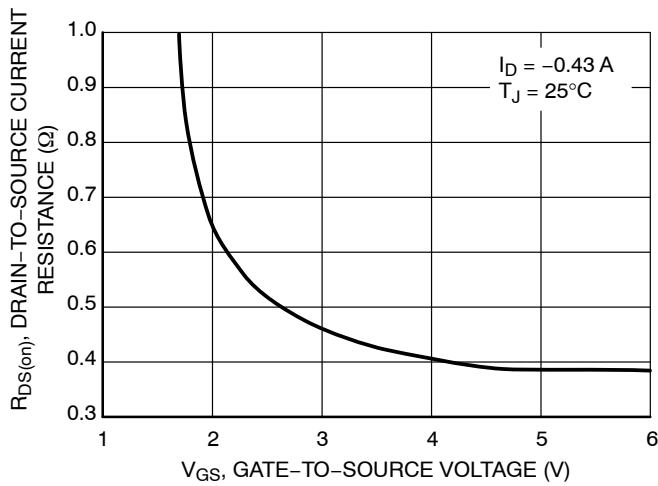


Figure 13. On-Resistance versus Gate-to-Source Voltage

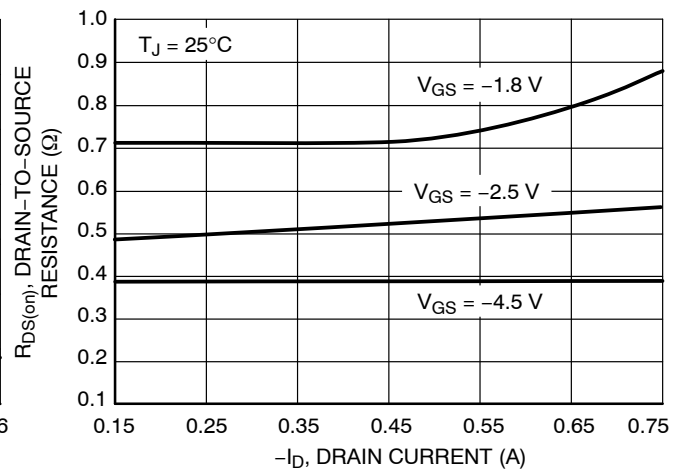


Figure 14. On-Resistance versus Drain Current and Gate Voltage

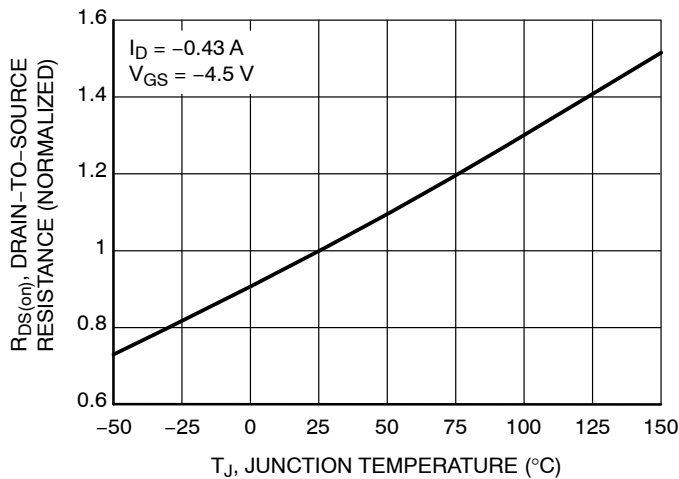


Figure 15. On-Resistance Variation with Temperature

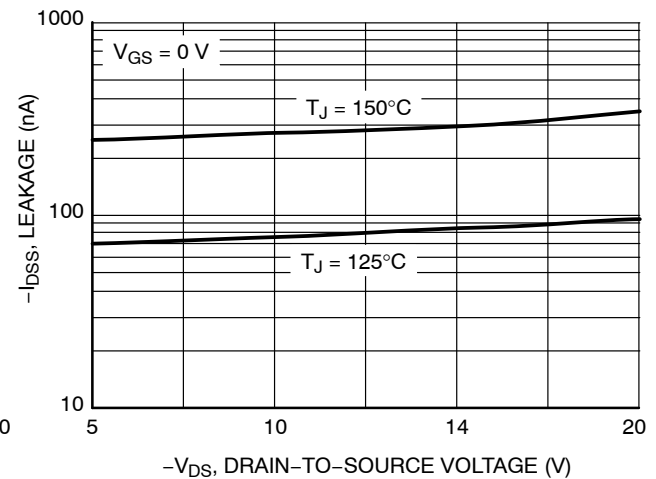


Figure 16. Drain-to-Source Leakage Current versus Voltage

P-CHANNEL TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

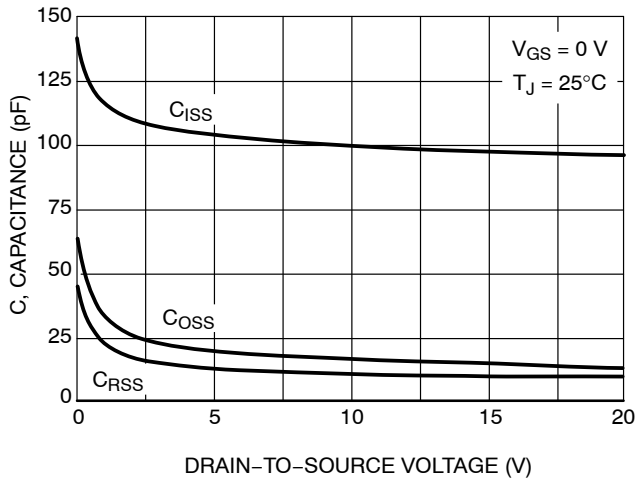


Figure 17. Capacitance Variation

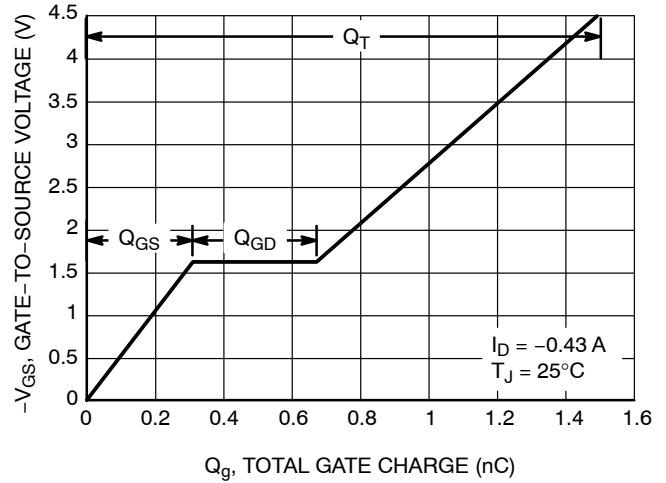


Figure 18. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

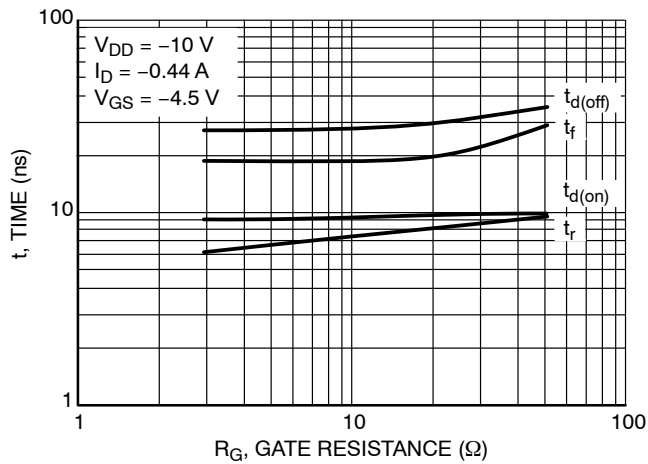


Figure 19. Resistive Switching Time Variation versus Gate Resistance

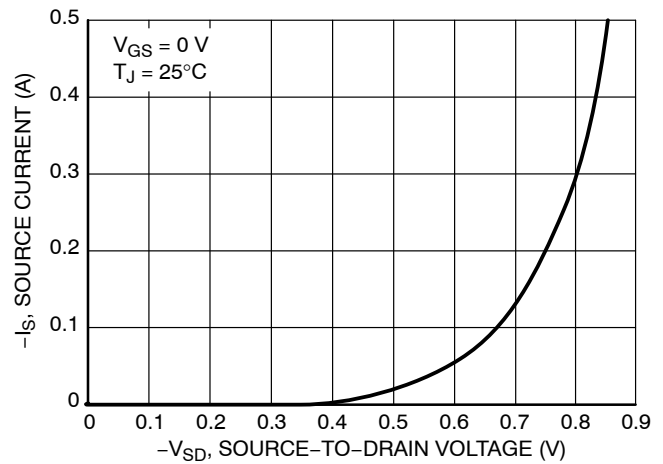
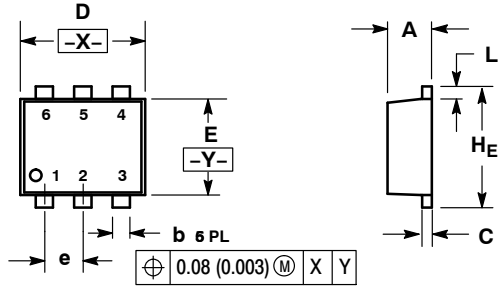


Figure 20. Diode Forward Voltage versus Current

NTZD3156C

PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A-01 ISSUE F



NOTES:

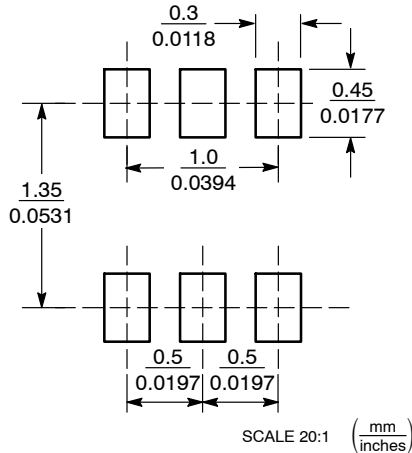
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H _E	1.50	1.60	1.70	0.059	0.062	0.066

STYLE 9:

- PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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